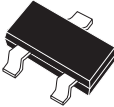


CMPT6428
CMPT6429

NPN SILICON TRANSISTOR



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT6428, CMPT6429 types are NPN Silicon Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high gain amplifier applications.

Marking Codes are C1K and C1L Respectively.

MAXIMUM RATINGS (T_A=25°C)

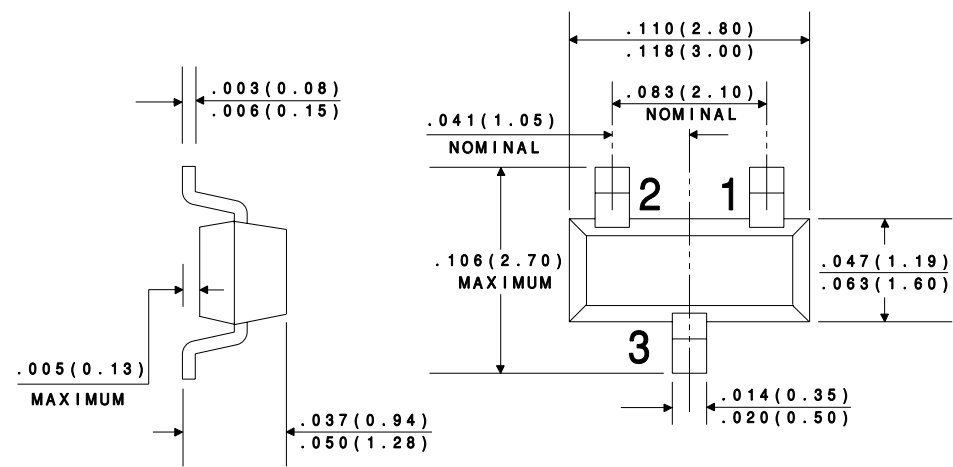
	SYMBOL	CMPT6428	CMPT6429	UNITS
Collector-Base Voltage	V _{CBO}	60	55	V
Collector-Emitter Voltage	V _{CEO}	50	45	V
Emitter-Base Voltage	V _{EBO}		6.0	V
Collector Current	I _C	200		mA
Power Dissipation	P _D	350		mW
Operating and Storage				
Junction Temperature	T _J , T _{stg}	-65 to +150		°C
Thermal Resistance	θ _{JA}	357		°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT6428		CMPT6429		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =30V		10		10	nA
I _{CEO}	V _{CE} =30V		100		100	nA
I _{EBO}	V _{BE} =5.0V		10		10	nA
BV _{CBO}	I _C =100μA		60		55	V
BV _{CEO}	I _C =1.0mA		50		45	V
V _{CE} (SAT)	I _C =10mA, I _B =0.5mA		0.20		0.20	V
V _{CE} (SAT)	I _C =100mA, I _B =5.0mA		0.60		0.60	V
V _{BE} (ON)	V _{CE} =5.0V, I _C =1.0mA	0.56	0.66	0.56	0.66	V
h _{FE}	V _{CE} =5.0V, I _C =10μA	250		500		
h _{FE}	V _{CE} =5.0V, I _C =100μA	250	650	500	1250	
h _{FE}	V _{CE} =5.0V, I _C =1.0mA	250		500		
h _{FE}	V _{CE} =5.0V, I _C =10mA	250		500		
f _T	V _{CE} =5.0V, I _C =1.0mA, f=100MHz	100	700	100	700	MHz

SYMBOL	TEST CONDITIONS	CMPT6428		CMPT6429		UNITS
		MIN	MAX	MIN	MAX	
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		3.0		3.0	pF
C _{ib}	V _{BE} =0.5V, I _C =0, f=1.0MHz		8.0		8.0	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR